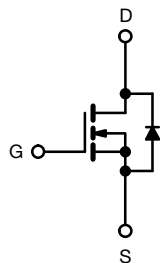
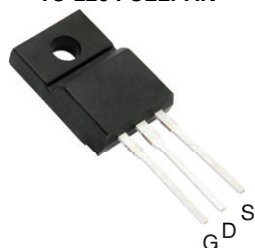


## Power MOSFET

**TO-220 FULLPAK**


N-Channel MOSFET

### FEATURES

- Isolated package
- High voltage isolation = 2.5 kV<sub>RMS</sub> (t = 60 s; f = 60 Hz)
- Sink to lead creepage distance = 4.8 mm
- 175 °C operating temperature
- Dynamic dV/dt rating
- Low thermal resistance
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### PRODUCT SUMMARY

|                          |                        |       |
|--------------------------|------------------------|-------|
| V <sub>DS</sub> (V)      | 60                     |       |
| R <sub>DS(on)</sub> (Ω)  | V <sub>GS</sub> = 10 V | 0.028 |
| Q <sub>g</sub> max. (nC) | 95                     |       |
| Q <sub>gs</sub> (nC)     | 27                     |       |
| Q <sub>gd</sub> (nC)     | 46                     |       |
| Configuration            | Single                 |       |

### DESCRIPTION

Third generation power MOSFETs from Vishay provides the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness.

The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

### ORDERING INFORMATION

|                |                |
|----------------|----------------|
| Package        | TO-220 FULLPAK |
| Lead (Pb)-free | IRFIZ44GPbF    |

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

| PARAMETER                                                 | SYMBOL                            | LIMIT                   | UNIT |
|-----------------------------------------------------------|-----------------------------------|-------------------------|------|
| Drain-source voltage                                      | V <sub>DS</sub>                   | 60                      | V    |
| Gate-source voltage                                       | V <sub>GS</sub>                   | ± 20                    |      |
| Continuous drain current                                  | V <sub>GS</sub> at 10 V           | T <sub>C</sub> = 25 °C  | A    |
|                                                           |                                   | T <sub>C</sub> = 100 °C |      |
| Pulsed drain current <sup>a</sup>                         | I <sub>DM</sub>                   | 120                     |      |
| Linear derating factor                                    |                                   | 0.32                    | W/°C |
| Single pulse avalanche energy <sup>b</sup>                | E <sub>AS</sub>                   | 100                     | mJ   |
| Maximum power dissipation                                 | P <sub>D</sub>                    | 48                      | W    |
| Peak diode recovery dV/dt <sup>c</sup>                    | dV/dt                             | 4.5                     | V/ns |
| Operating junction and storage temperature range          | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175             | °C   |
| Soldering recommendations (peak temperature) <sup>d</sup> | For 10 s                          | 300                     |      |
| Mounting torque                                           | M3 screw                          | 0.6                     | Nm   |

#### Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. V<sub>DD</sub> = 25 V, starting T<sub>J</sub> = 25 °C, L = 129 μH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 30 A (see fig. 12)

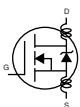
c. I<sub>SD</sub> ≤ 52 A, dI/dt ≤ 250 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 175 °C

d. 1.6 mm from case

**THERMAL RESISTANCE RATINGS**

| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum junction-to-ambient      | $R_{thJA}$ | -    | 65   | °C/W |
| Maximum junction-to-case (drain) | $R_{thJC}$ | -    | 3.1  |      |

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER                                 | SYMBOL                           | TEST CONDITIONS                                                                                                                                                     |                                                                                  | MIN. | TYP.  | MAX.  | UNIT |
|-------------------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------|------|-------|-------|------|
| Static                                    |                                  |                                                                                                                                                                     |                                                                                  |      |       |       |      |
| Drain-ssource breakdown voltage           | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                                                                      |                                                                                  | 60   | -     | -     | V    |
| V <sub>DS</sub> temperature coefficient   | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA                                                                                                                           |                                                                                  | -    | 0.060 | -     | V/°C |
| Gate-source threshold voltage             | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                                                         |                                                                                  | 2.0  | -     | 4.0   | V    |
| Gate-source leakage                       | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 20 V                                                                                                                                            |                                                                                  | -    | -     | ± 100 | nA   |
| Zero gate voltage drain current           | I <sub>DSS</sub>                 | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V                                                                                                                       |                                                                                  | -    | -     | 25    | μA   |
|                                           |                                  | V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C                                                                                              |                                                                                  | -    | -     | 250   |      |
| Drain-source on-state resistance          | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 10 V                                                                                                                                              | I <sub>D</sub> = 18 A <sup>b</sup>                                               | -    | -     | 0.028 | Ω    |
| Forward transconductance                  | g <sub>fs</sub>                  | V <sub>DS</sub> = 25 V, I <sub>D</sub> = 18 A <sup>b</sup>                                                                                                          |                                                                                  | 15   | -     | -     | S    |
| Dynamic                                   |                                  |                                                                                                                                                                     |                                                                                  |      |       |       |      |
| Input capacitance                         | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 25 V,<br>f = 1.0 MHz, see fig. 5                                                                                        |                                                                                  | -    | 2500  | -     | pF   |
| Output capacitance                        | C <sub>oss</sub>                 |                                                                                                                                                                     |                                                                                  | -    | 1200  | -     |      |
| Reverse transfer capacitance              | C <sub>rss</sub>                 |                                                                                                                                                                     |                                                                                  | -    | 200   | -     |      |
| Drain to sink capacitance                 | C                                | f = 1.0 MHz                                                                                                                                                         |                                                                                  | -    | 12    | -     |      |
| Total gate charge                         | Q <sub>g</sub>                   | V <sub>GS</sub> = 10 V                                                                                                                                              | I <sub>D</sub> = 52 A, V <sub>DS</sub> = 48 V,<br>see fig. 6 and 13 <sup>b</sup> | -    | -     | 95    | nC   |
| Gate-source charge                        | Q <sub>gs</sub>                  |                                                                                                                                                                     |                                                                                  | -    | -     | 27    |      |
| Gate-drain charge                         | Q <sub>gd</sub>                  |                                                                                                                                                                     |                                                                                  | -    | -     | 46    |      |
| Turn-on delay time                        | t <sub>d(on)</sub>               | V <sub>DD</sub> = 30 V, I <sub>D</sub> = 52 A,<br>R <sub>G</sub> = 9.1 Ω, R <sub>D</sub> = 0.54 Ω,<br>see fig. 10 <sup>b</sup>                                      |                                                                                  | -    | 19    | -     | ns   |
| Rise time                                 | t <sub>r</sub>                   |                                                                                                                                                                     |                                                                                  | -    | 120   | -     |      |
| Turn-off delay time                       | t <sub>d(off)</sub>              |                                                                                                                                                                     |                                                                                  | -    | 55    | -     |      |
| Fall time                                 | t <sub>f</sub>                   |                                                                                                                                                                     |                                                                                  | -    | 86    | -     |      |
| Internal drain inductance                 | L <sub>D</sub>                   | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact<br> |                                                                                  | -    | 4.5   | -     | nH   |
| Internal source inductance                | L <sub>S</sub>                   |                                                                                                                                                                     |                                                                                  | -    | 7.5   | -     |      |
| Drain-Source Body Diode Characteristics   |                                  |                                                                                                                                                                     |                                                                                  |      |       |       |      |
| Continuous source-drain diode current     | I <sub>S</sub>                   | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode<br>   |                                                                                  | -    | -     | 30    | A    |
| Pulsed diode forward current <sup>a</sup> | I <sub>SM</sub>                  |                                                                                                                                                                     |                                                                                  | -    | -     | 120   |      |
| Body diode voltage                        | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 30 A, V <sub>GS</sub> = 0 V <sup>b</sup>                                                                                   |                                                                                  | -    | -     | 2.5   | V    |
| Body diode reverse recovery time          | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = 52 A, dI/dt = 100 A/μs <sup>b</sup>                                                                                        |                                                                                  | -    | 140   | 300   | ns   |
| Body diode reverse recovery charge        | Q <sub>rr</sub>                  |                                                                                                                                                                     |                                                                                  | -    | 1.2   | 2.8   | μC   |
| Forward turn-on time                      | t <sub>on</sub>                  | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )                                                                   |                                                                                  |      |       |       |      |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

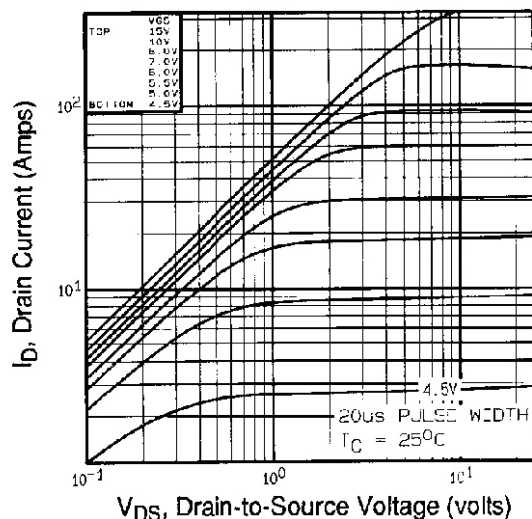


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^{\circ}\text{C}$

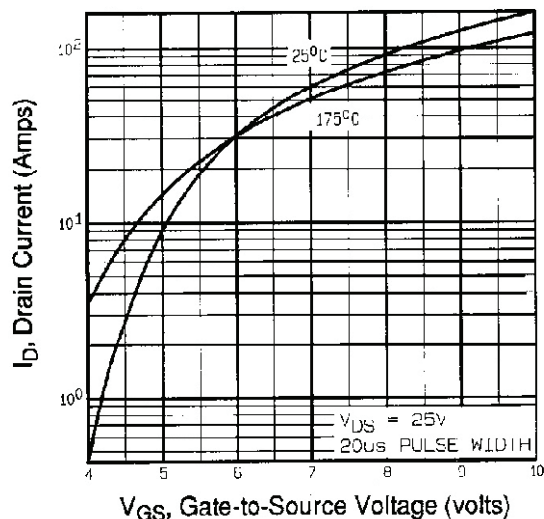


Fig. 3 - Typical Transfer Characteristics

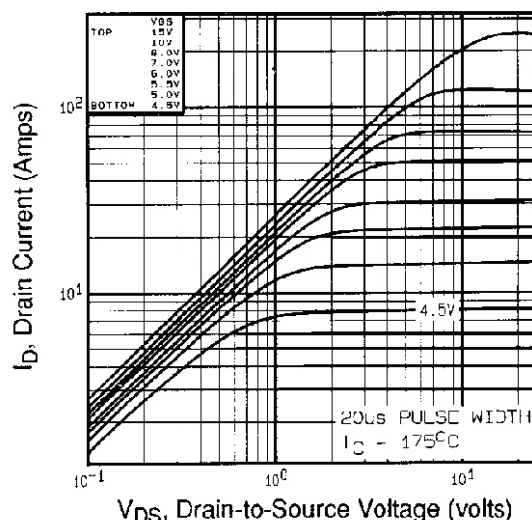


Fig. 2 - Typical Output Characteristics,  $T_C = 175\text{ }^{\circ}\text{C}$

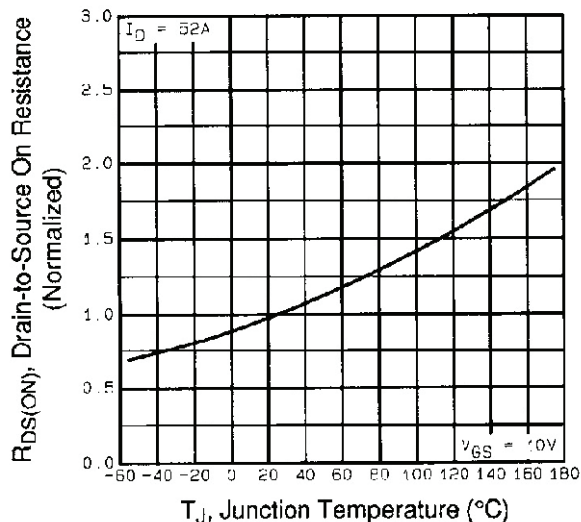
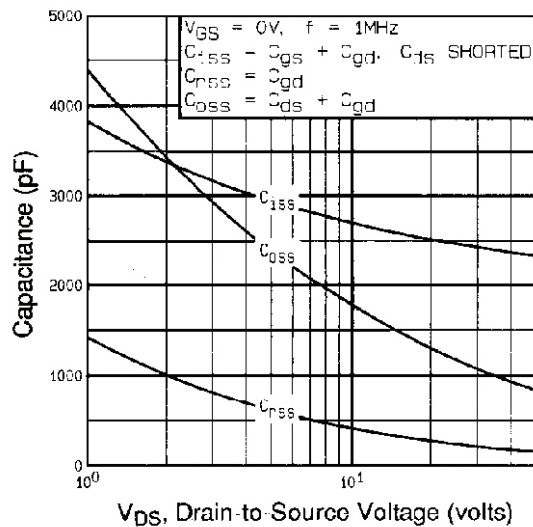
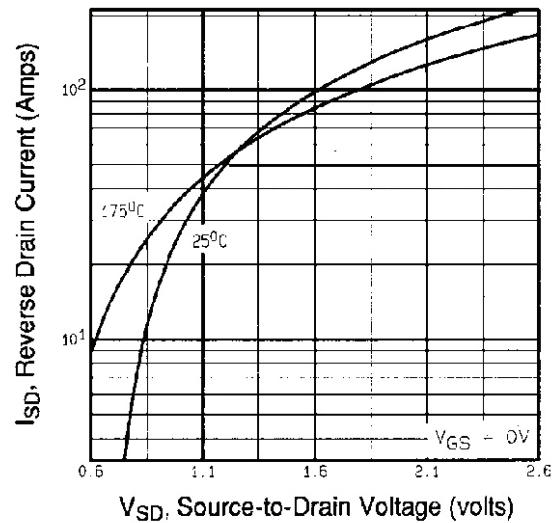
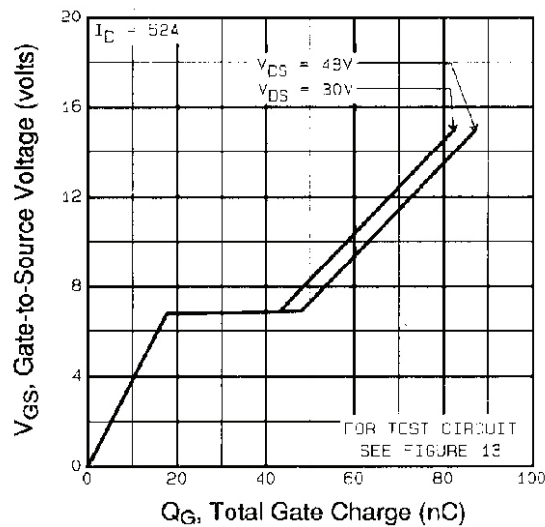
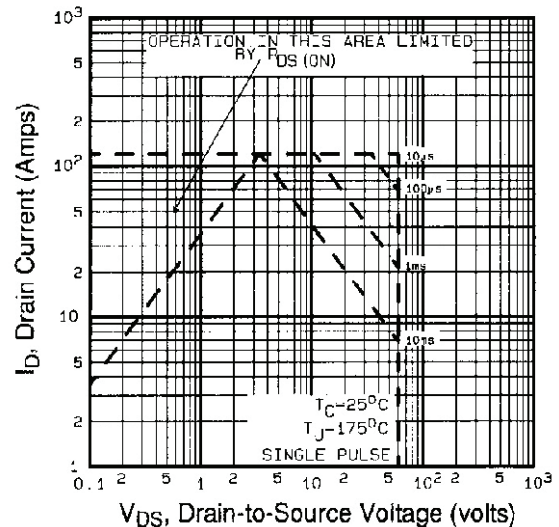
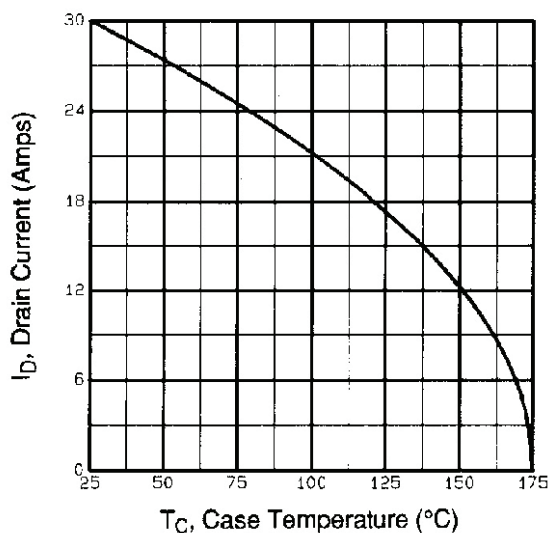
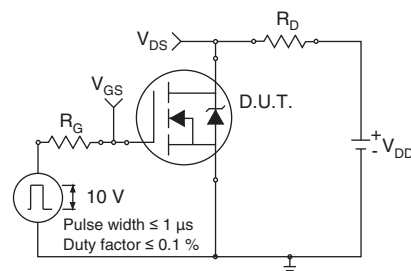
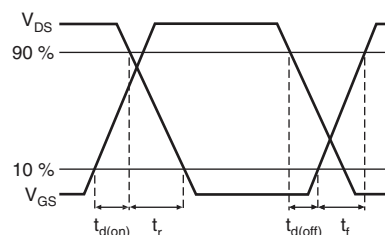
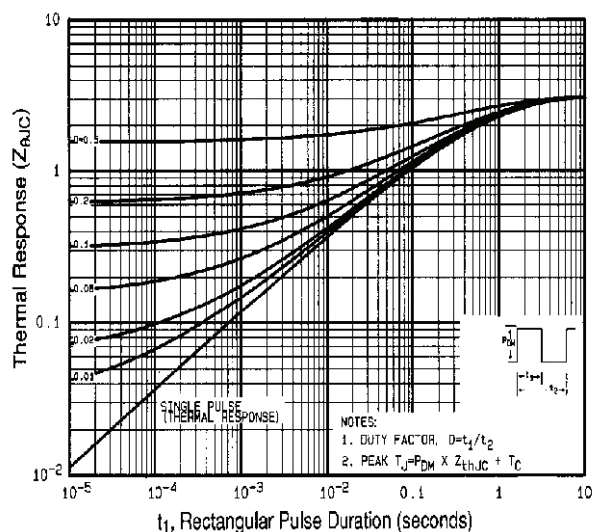
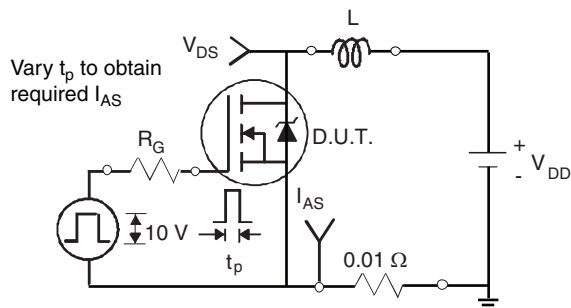
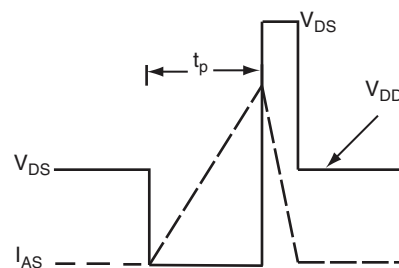
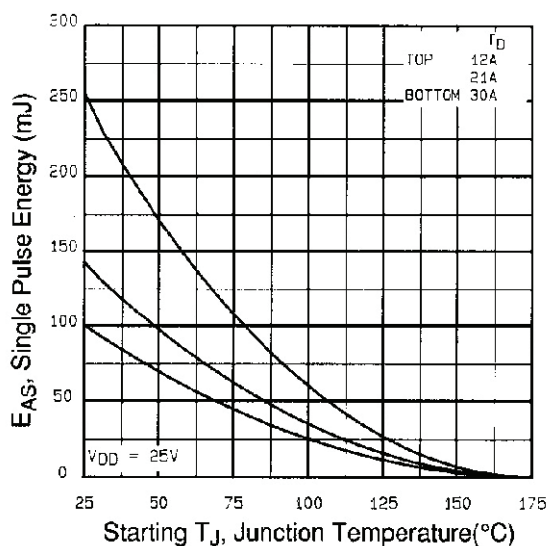


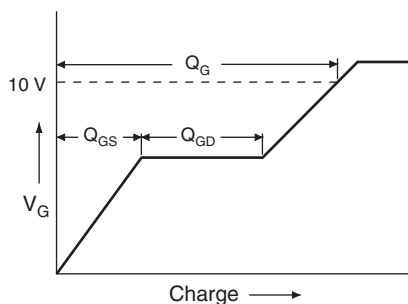
Fig. 4 - Normalized On-Resistance vs. Temperature


**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 8 - Maximum Safe Operating Area**

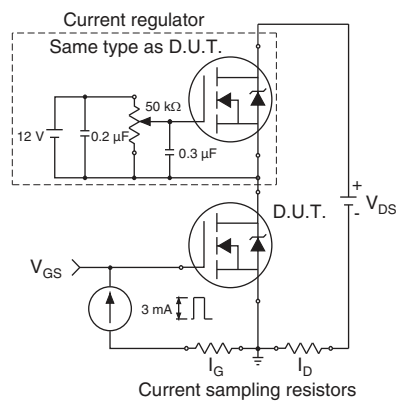

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 10a - Switching Time Test Circuit**

**Fig. 10b - Switching Time Waveforms**

**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Fig. 12a - Unclamped Inductive Test Circuit**

**Fig. 12b - Unclamped Inductive Waveforms**



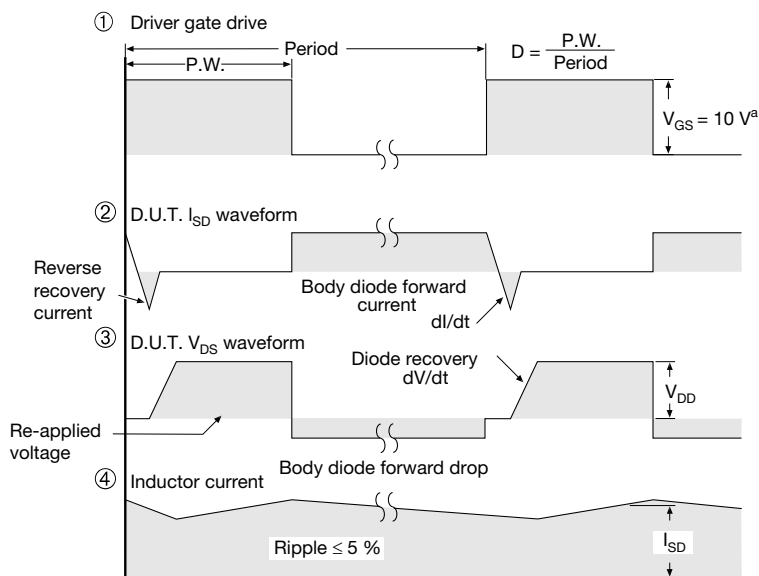
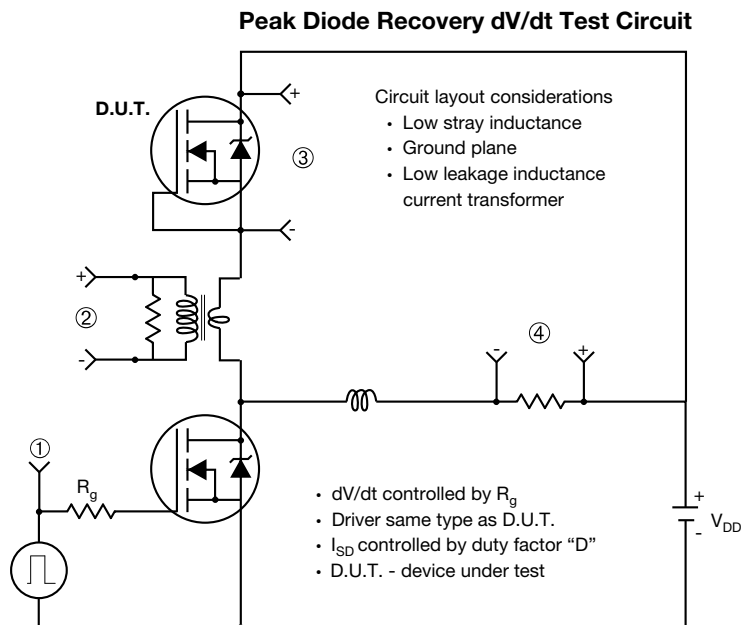
**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**



**Fig. 13a - Basic Gate Charge Waveform**



**Fig. 13b - Gate Charge Test Circuit**



#### Note

a.  $V_{GS} = 5 V$  for logic level devices

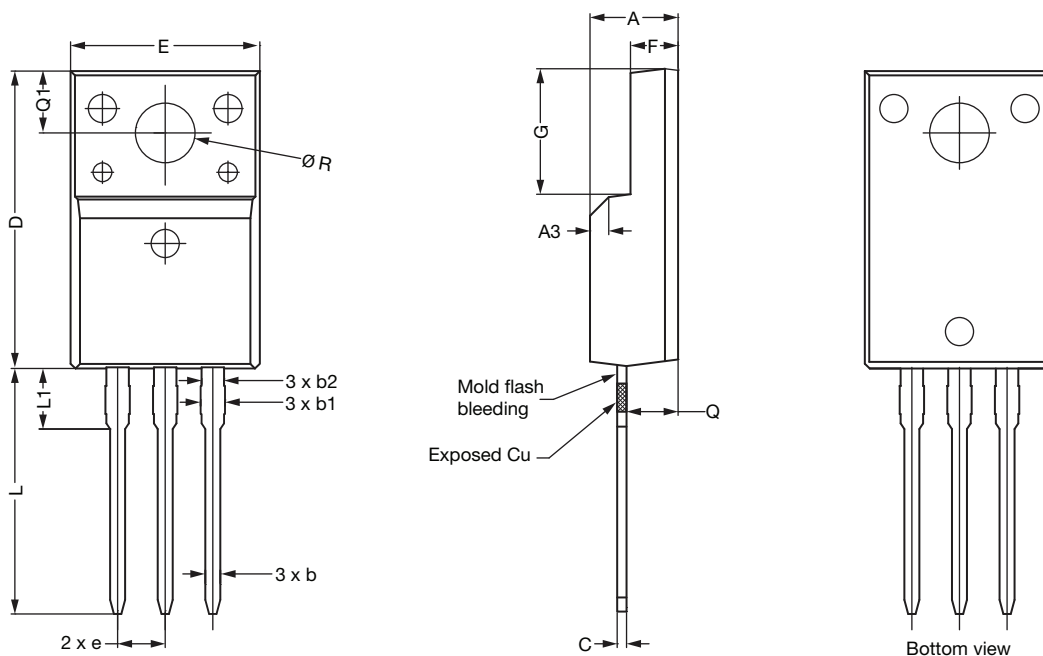
**Fig. 14 - For N-Channel**

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## TO-220 FULLPAK (High Voltage)

### OPTION 1: FACILITY CODE = 9

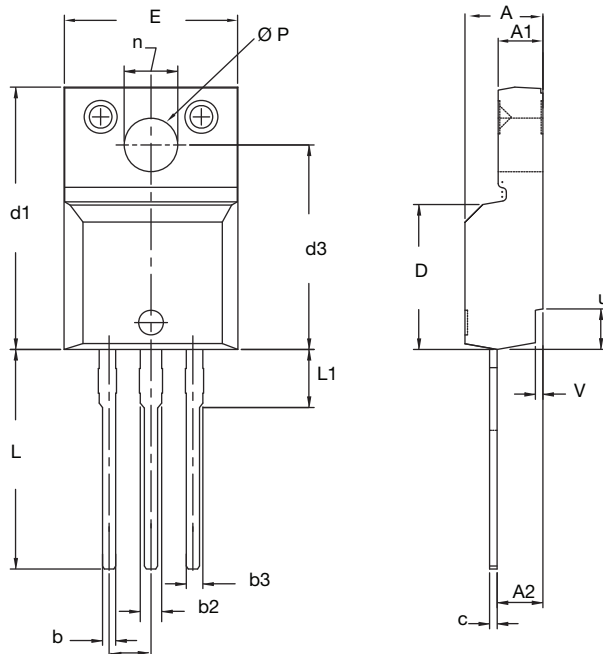


| DIM. | MILLIMETERS |       |       |
|------|-------------|-------|-------|
|      | MIN.        | NOM.  | MAX.  |
| A    | 4.60        | 4.70  | 4.80  |
| b    | 0.70        | 0.80  | 0.91  |
| b1   | 1.20        | 1.30  | 1.47  |
| b2   | 1.10        | 1.20  | 1.30  |
| C    | 0.45        | 0.50  | 0.63  |
| D    | 15.80       | 15.87 | 15.97 |
| e    | 2.54 BSC    |       |       |
| E    | 10.00       | 10.10 | 10.30 |
| F    | 2.44        | 2.54  | 2.64  |
| G    | 6.50        | 6.70  | 6.90  |
| L    | 12.90       | 13.10 | 13.30 |
| L1   | 3.13        | 3.23  | 3.33  |
| Q    | 2.65        | 2.75  | 2.85  |
| Q1   | 3.20        | 3.30  | 3.40  |
| Ø R  | 3.08        | 3.18  | 3.28  |

#### Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet  $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1<sup>st</sup> character located at the 2<sup>nd</sup> row of the unit marking



**OPTION 2: FACILITY CODE = Y**

| DIM. | MILLIMETERS |        | INCHES    |       |
|------|-------------|--------|-----------|-------|
|      | MIN.        | MAX.   | MIN.      | MAX.  |
| A    | 4.570       | 4.830  | 0.180     | 0.190 |
| A1   | 2.570       | 2.830  | 0.101     | 0.111 |
| A2   | 2.510       | 2.850  | 0.099     | 0.112 |
| b    | 0.622       | 0.890  | 0.024     | 0.035 |
| b2   | 1.229       | 1.400  | 0.048     | 0.055 |
| b3   | 1.229       | 1.400  | 0.048     | 0.055 |
| c    | 0.440       | 0.629  | 0.017     | 0.025 |
| D    | 8.650       | 9.800  | 0.341     | 0.386 |
| d1   | 15.88       | 16.120 | 0.622     | 0.635 |
| d3   | 12.300      | 12.920 | 0.484     | 0.509 |
| E    | 10.360      | 10.630 | 0.408     | 0.419 |
| e    | 2.54 BSC    |        | 0.100 BSC |       |
| L    | 13.200      | 13.730 | 0.520     | 0.541 |
| L1   | 3.100       | 3.500  | 0.122     | 0.138 |
| n    | 6.050       | 6.150  | 0.238     | 0.242 |
| Ø P  | 3.050       | 3.450  | 0.120     | 0.136 |
| u    | 2.400       | 2.500  | 0.094     | 0.098 |
| V    | 0.400       | 0.500  | 0.016     | 0.020 |

ECN: E19-0180-Rev. D, 08-Apr-2019  
DWG: 5972

**Notes**

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet  $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1<sup>st</sup> character located at the 2<sup>nd</sup> row of the unit marking



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